

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2544	(349/43,42).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/21 09:00
L2	11	L1 and (scan\$4 adj line) near3 extension	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/21 09:01
L3	4279	(257/72,344,408,51,65,73,381).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/21 07:40
L4	4	L3 and (scan\$4 adj line) near3 extension	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/21 07:40
L5	2691	(349/43,42,44).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/21 09:00
L6	15	L5 and (scan\$4 adj line) near3 extension	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/21 09:01
L7	4	6 not 2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/21 09:01
S1	42	(multi-gate multi?gate multi near gate) near3 thin near film near transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/20 15:00
S2	33	S1 and (lcd liquid near crystal near display)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/20 15:00

S3	2	S2 and polycrystalline near silicon near layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/20 15:00
S4	1	S3 and gate near channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/20 15:00
S5	2	("5693959").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/20 14:57
S6	45	(multi-gate multi?gate multi near gate) near3 thin near film near transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/20 15:02
S7	34	S6 and (lcd liquid near crystal near display)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/20 15:00
S8	2	S7 and polycrystalline near silicon near layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/20 15:03
S9	1	S8 and gate near channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/20 15:01
S10	430	(multi-gate multi?gate multi near gate) near3 ((thin near film near transistor) tft lcd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/20 15:02
S11	16	S10 and polycrystalline near silicon near layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/20 15:04
S12	16	S11 and shap\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/20 15:03

S13	5	S10 and (polycrystalline near silicon near layer) near5 shap\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/20 15:04
S14	5	S10 and (polycrystalline near silicon near layer) near3 shap\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/20 16:23
S15	5	S10 and (polycrystalline near silicon near layer) with shap\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/20 15:04
S16	1	S10 and (polycrystalline near silicon near layer) near shap\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/20 15:05
S17	4267	(257/72,344,408,51,65,73,381).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/20 16:31
S18	6390	(438/48,128,149,151,157,166, 283,307,570).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/20 16:33
S19	2543	(349/43,42).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/20 16:34
S20	379	S10 and LDD	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/20 16:36
S21	78	S20 and scan\$4 adj line	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/20 16:41
S22	3	S20 and (scan\$4 adj line) near3 extension	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/20 17:31

S23	78	S21 and gate and (source drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/20 17:21
S24	18	S23 and lcd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/20 17:21
S25	11	S19 and (scan\$4 adj line) near3 extension	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/21 07:39